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INVENTCHIP TECHNOLOGY

IVCR2504 24V 5A Peak Source and Sink Dual-Channel Driver

1. Features

- Industry standard SOIC-8 pinout
- Two independent gate drive channels
- 5A source and sink peak drive current
- Wide VDD range up to 24V
- Separated enable inputs
- Two channels in parallel for high current driving
- VDD UVLO protection
- TTL and CMOS compatible inputs
- Low propagation delays
- 1ns typical delay matching between two channels
- Outputs held low when floating inputs
- Operating temperature range -40°C to 125°C

2. Applications

- AC/DC and DC/DC converters
- Server and Telecom rectifiers
- EV/HEV inverters and DC/DC converters
- PV boosters and inverters
- UPS
- Motor Control
- Emerging Wide Band-Gap Power Devices

3. Description

The IVCR2504 is a 5A dual-channel, high-speed, low-side gate driver, capable of effectively and safely driving MOSFETs and IGBTs. Low propagation delay and mismatch and compact SOIC-8 package enables MOSFETs to switch at hundreds of kHz. It is very suitable for server and telecom power supply's synchronous rectification driving, where synchronous MOSFET's dead time accuracy directly impacts converter's efficiency. The driver is capable to parallel two channels to increase output driving current. The input thresholds are based on TTL with voltage tolerance from -5V to 20V.

Wide VDD operating range from 4.5V to 20V enables effective driving with MOSFET or GaN power switches. Integrated UVLO protection ensures output held at low under abnormal conditions.

The independent inputs ranges from -5V to 24V ensure robust operation with undershoot or overshoot induced by parasitic inductances. The input thresholds are compatible with TTL input.

Device Information

PART NUMBER	PACKAGE	PACKING
IVCR2504DR	SOIC-8	Tape and Reel
IVCR2504D	SOIC-8	Tube

Pin Configuration

Dual Non-Inverting Inputs

IVCR2504

Table of Contents

4. Pin Configuration and Functions

PIN	NAME	I/O	DESCRIPTION
1	ENA	I	Channel A enable input
2	INA	I	Channel A input
3	GND	G	Driver ground
4	INB	I	Channel B input
5	OUTB	O	Channel B driver output
6	VDD	P	Positive bias supply
7	OUTA	O	Channel A driver output
8	ENB	I	Channel B enable input

Truth Table

VDD is higher than UVLO threshold.

ENx	INx	OUTx
L	X	L
H or floating	L or floating	L
H or floating	H	H

5. Specifications

5.1 Absolute Maximum Ratings

Over free-air temperature range (unless otherwise noted) [1]

		MIN	MAX	UNIT
V_{DD}	Total supply voltage (reference to GND)	-0.3	24	V
OUTA, OUTB	Gate driver output voltage	-0.3	V_{DD}+0.3	V
INA, INB	Signal input voltage	-5	24	V
ENA, ENB	Enable control signal	-5	24	V
T_J	Junction temperature	-40	150	°C
T_{STG}	Storage temperature	-65	150	°C

(1) Operating beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended period may affect device reliability.

5.2 ESD Rating

			Value	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001[1]	+/-2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101[2]	+/-500	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operation Conditions

		MIN	MAX	UNIT
V_{DD}	Supply voltage	4.5	20	V
$V_{INx, ENx}$	Input voltage	0	20	V
T_A	Ambient temperature	-40	125	°C

5.4 Thermal Information

			UNIT
$R_{\theta JA}$	Junction-to-Ambient	128	°C/W
$R_{\theta JB}$	Junction-to-PCB	68.5	°C/W

5.5 Electrical Specifications

Unless otherwise noted, V_{DD} = 12 V, T_A = –40°C to 125°C
Currents are positive into and negative out of the specified terminal. Typical condition specifications are at 25°C.

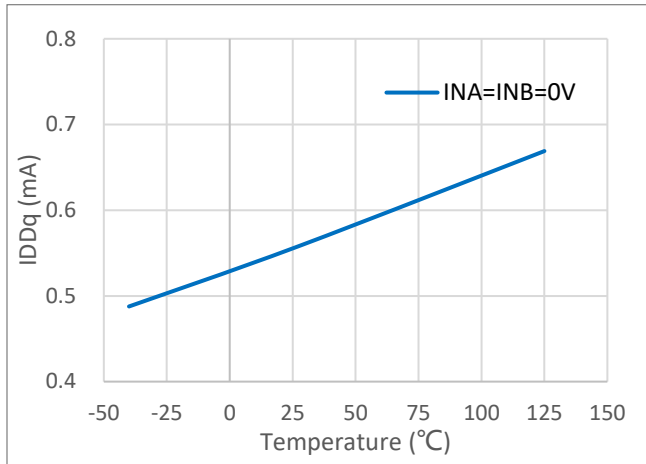| PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
BIAS CURRENT						
I_{DDoff}	Startup current	VDD=3V, INA=INB=0V		30		μA
I_{DDq}	Quiescent current	INA=INB=0V		0.6		mA
UVLO						
V_{ON}	Under voltage	Rising threshold		3.8	4.2	V
V_{OFF}	thresholds	Falling threshold	3.2	3.5		
INPUT (INA, INB)						
V_{INH}	Input rising threshold			1.96	2.4	V
V_{INL}	Input falling threshold		0.8	1.15		V
V_{INHYS}	Input hysteresis			0.8		V
V_{INNS}	Input negative voltage capability		-5			V
ENABLE INPUT (ENA, ENB)						
V_{ENH}	Enable input rising threshold			1.92	2.2	V
V_{ENL}	Enable input signal threshold		0.8	1.2		V
V_{INHYS}	Enable input hysteresis			0.7		V
OUTPUTS (OUTA, OUTB)						
I_O	Peak source and sink currents	C_{LOAD} =0.22uF, with external current limiting resistors, 1kHz switching frequency		5		A
V_{OH}	Output high voltage	I_{OUTH} = -10mA		V_{DD}-0.007	V_{DD}-0.03	V
V_{OL}	Output low voltage	I_{OUTL} = 10mA		0.005	0.012	V
R_{OH}	Output static pull-up resistance			0.7	3	Ω
R_{OL}	Output pull-down resistance			0.5	1.2	Ω
Timing						
TD_{rr}	Rising delay	C_{LOAD} = 1.8nF		16	30	ns
TD_{ff}	Falling delay			16	30	
T_r	Rise time	C_{LOAD} = 1.8nF		8	12	ns
T_f	Fall time			8	12	
T_{dm}	Delay mismatch	INA=INB, ENA=ENB=VDD		1		ns

6. Typical Characteristics

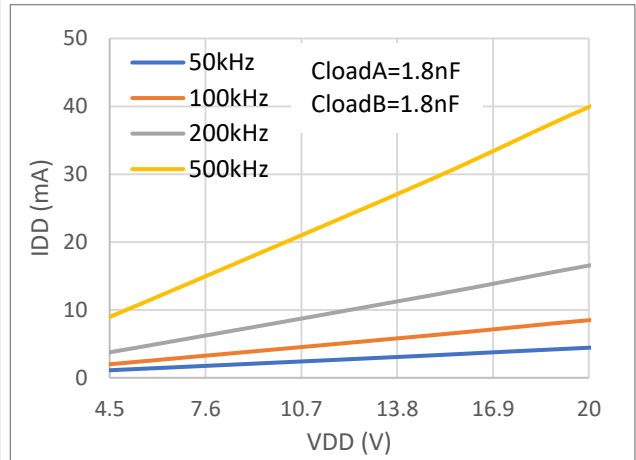**Figure 1. Quiescent Current IDDq vs Temperature**
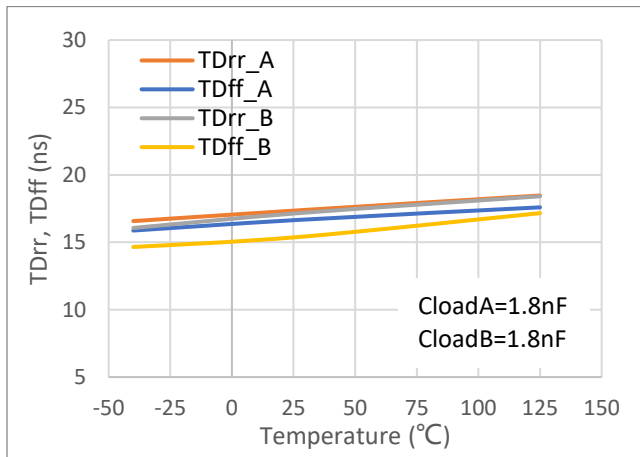
Figure 2. Operating Current IDD vs VDD

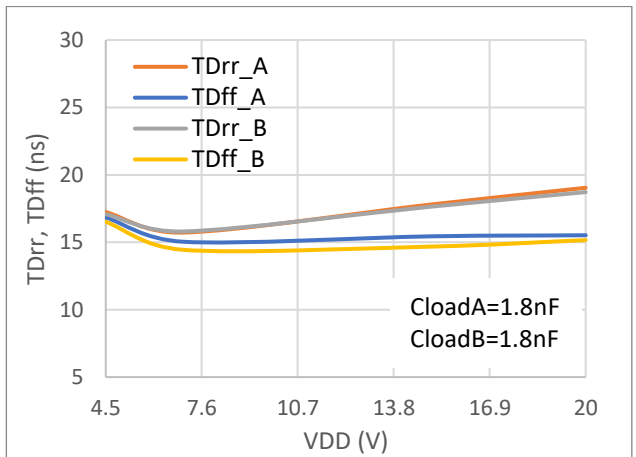**Figure 3. Propagation Delay vs Temperature**
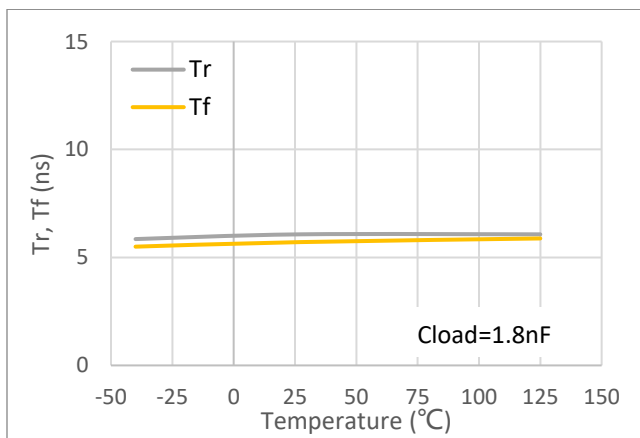
Figure 4. Propagation Delay vs VDD

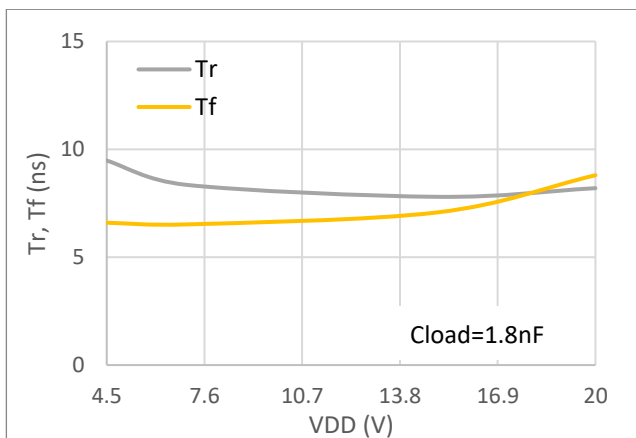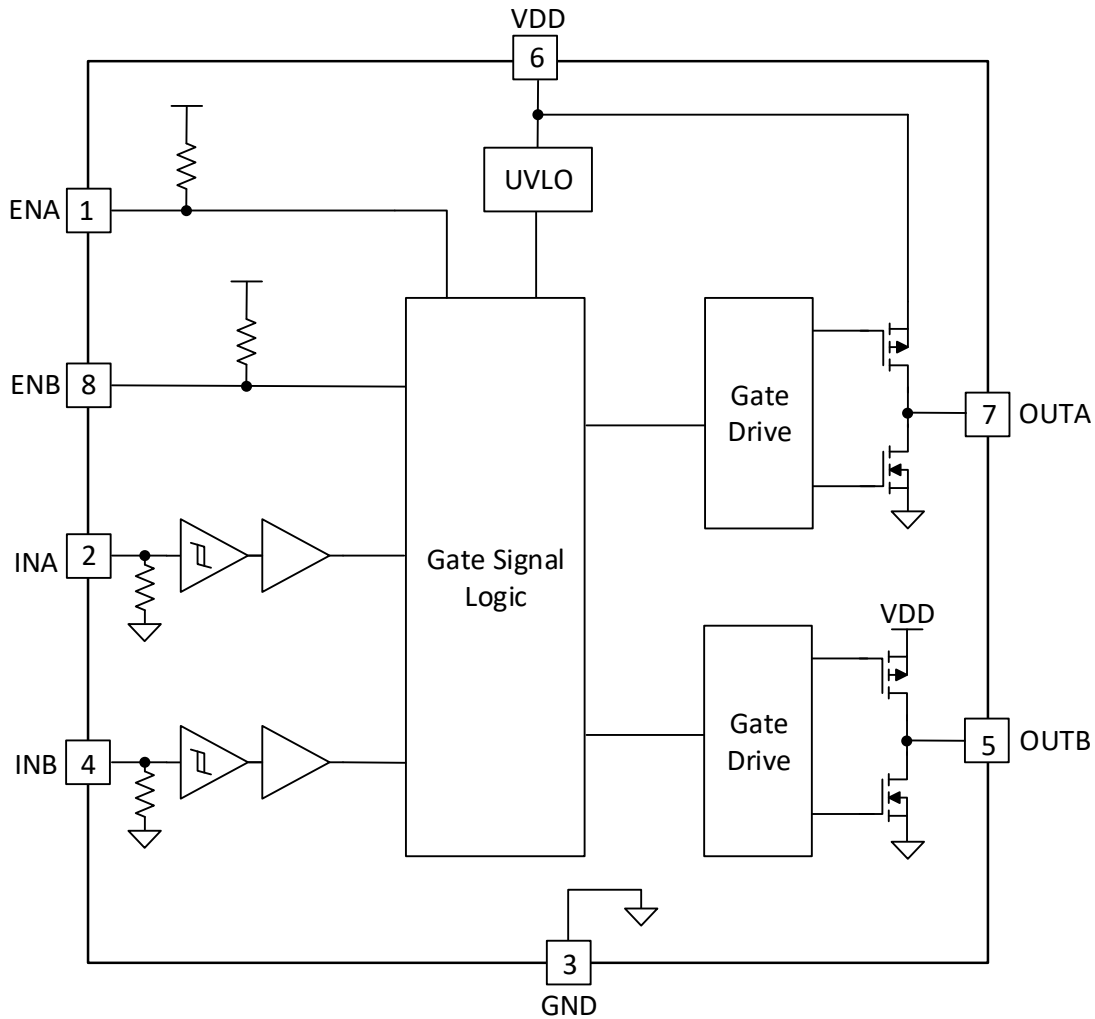**Figure 5. Rise Time and Fall time vs Temperature**

Figure 6. Rise Time and Fall time vs VDD

7. Detail Descriptions

IVCR2504 driver provides dual-channel high-speed low-side gate drive. It features tight mismatching outputs when two channels are paralleled to drive large or paralleled power switches.

Function Block Diagram

7.1 Input Signals INA and INB

INA and INB are non-inverting logic gate driver inputs. The pins have a weak pulldown. When left floating, outputs are pulled to GND. The input is a TTL and CMOS logic level with maximum 24V input tolerance.

7.2 Enable Signals ENA and ENB

ENA and ENB are enable control signals. When ENx is driven low the OUTx is pulled to GND. When ENx is driven high the OUTx follows INx. The enable pins have a weak pullup. When left floating, outputs follow inputs. The enable signal is a TTL and CMOS logic level with maximum 24V input tolerance.
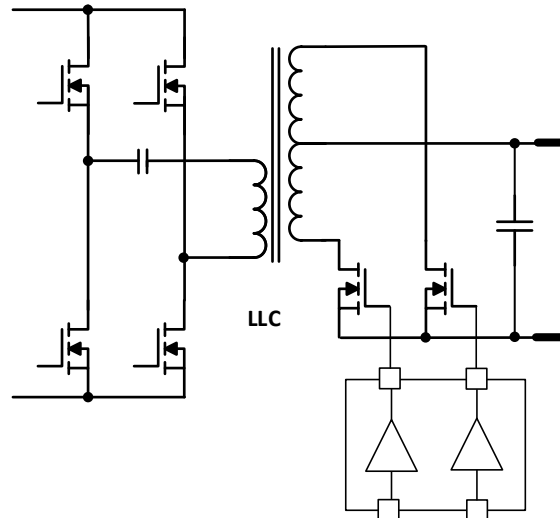
7.3 OUTA and OUTB

OUTA and OUTB are totem-pole outputs, which consist of a P-channel MOSFET for pullup and an N-channel MOSFET for pulldown. Each output stage in IVCR2504 can supply 5A peak source and 5A peak sink current pulses. The output voltage swings between VDD and GND providing rail-to-rail operation. The presence of the MOSFET body diodes also offer voltage clamping paths to limit overshoot and undershoot. That means that in many cases, external Schottky diode clamps may not be necessary.
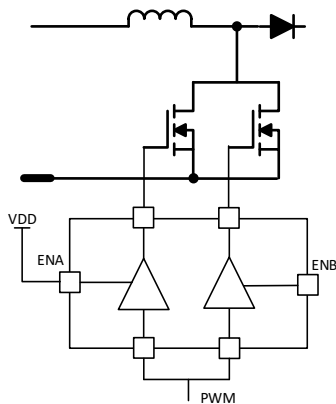
7.4 VDD and Under Voltage Protection

IVCR2504 maximum voltage rating is 24V. It is suitable for Si MOSFET, IGBT and SiC MOSFET gate drive. The driver has internal under voltage lockout (UVLO) protection feature. When VDD level is below UVLO threshold, this circuit holds the output LOW, regardless of the status of the inputs.
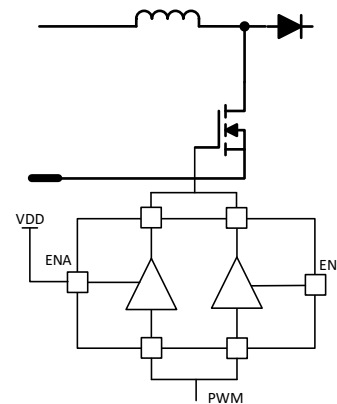
8. Application Implementation
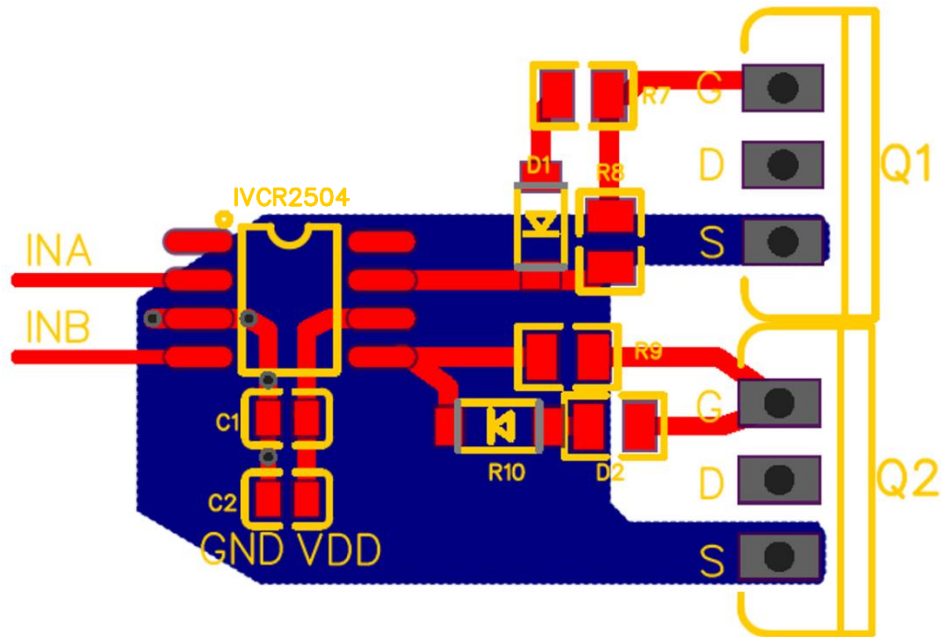
Two channels driven separately

Two paralleled switches driven by
two outputs with minimized mismatch

A large switch driven by two paralleled
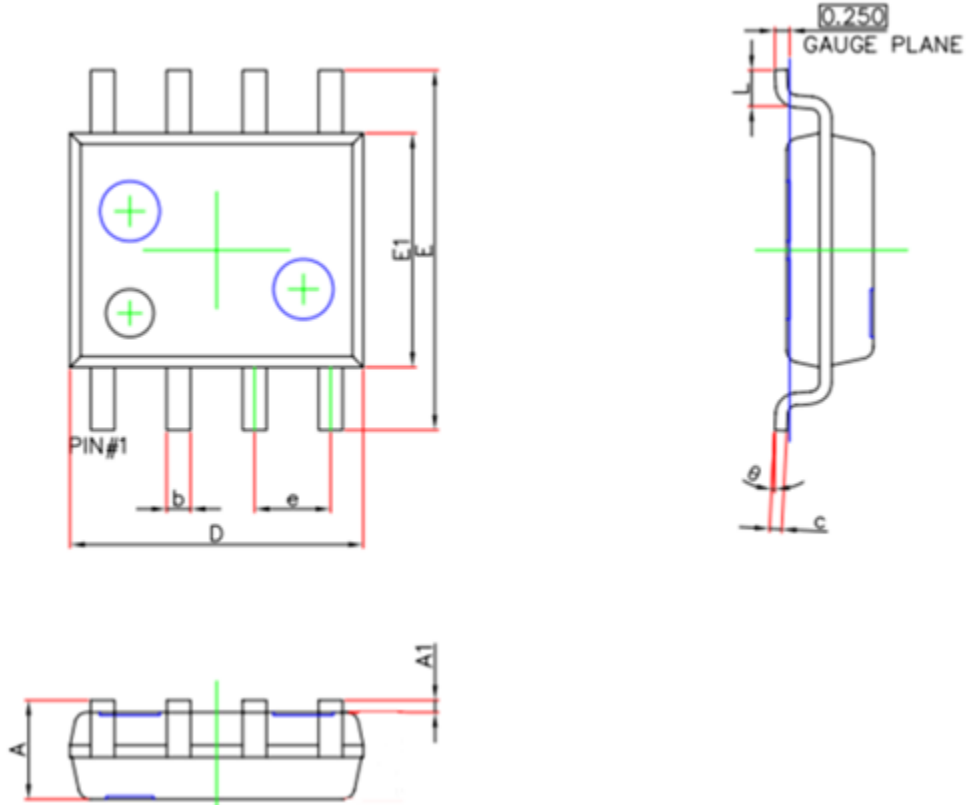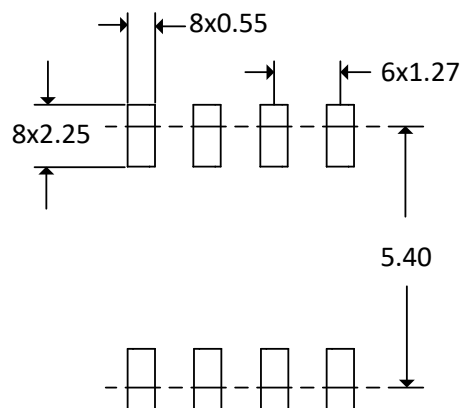outputs with minimized mismatch

9. Layout

Layout Example for IVCR2504

10. Package Information

SOIC-8 Package Dimensions

Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.110	0.250	0.004	0.010
b	0.310	0.510	0.012	0.020
c	0.130	0.250	0.005	0.010
D	4.810	5.000	0.189	0.197
E	5.800	6.190	0.228	0.244
E1	3.810	3.980	0.150	0.157
e	1.270		0.050	
L	0.410	1.270	0.016	0.050
θ	0.000	8.000	0.000	0.315

SOIC-8 Recommended Soldering Dimensions